



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	56	∇ C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	180	∇ C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	



Pulsed Drain Current	I_{DM}	18	A
Total Power Dissipation	$P_D@T_C=25$	2.2	W
Total Power Dissipation	$P_D@T_A=25$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	35	mJ

P Channel Absolute Maximum Ratings



Input capacitance	Ciss	f = 1MHz V _{DS} =25V	-	1150	-	pF
Output capacitance	Coss		-	290	-	
Reverse transfer capacitance	Crss		-			

N Channel characteristics curve

Fig.1 Power Dissipation Derating Curve

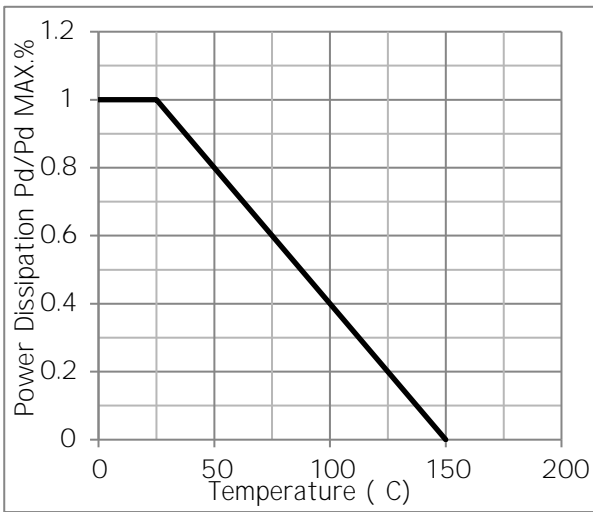


Fig.2 Typical output Characteristics

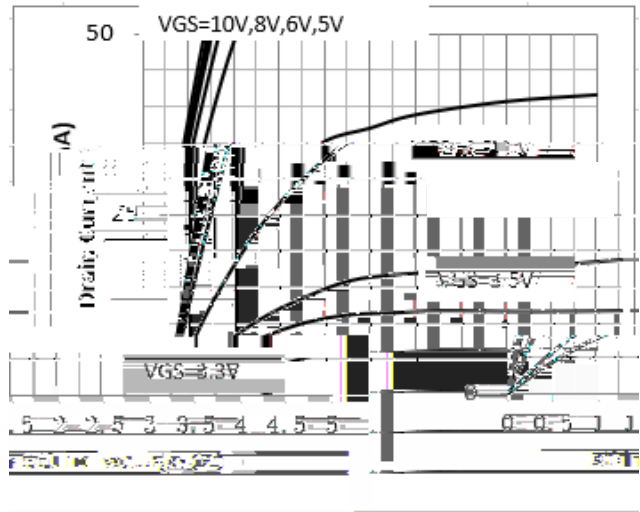


Fig.3 Threshold Voltage V.S Junction Temperature

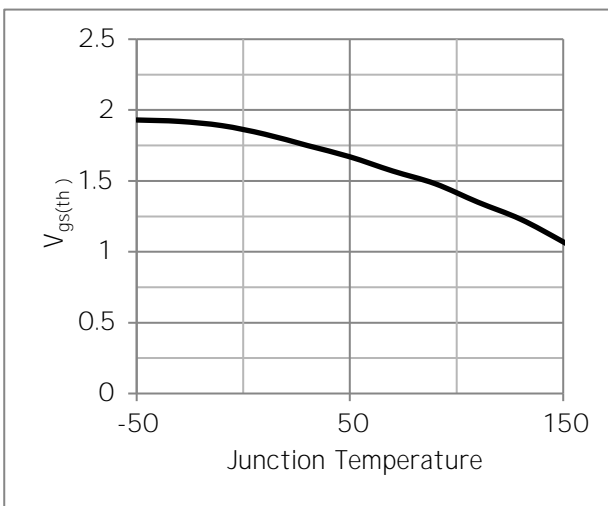


Fig.4 Resistance V.S Drain Current

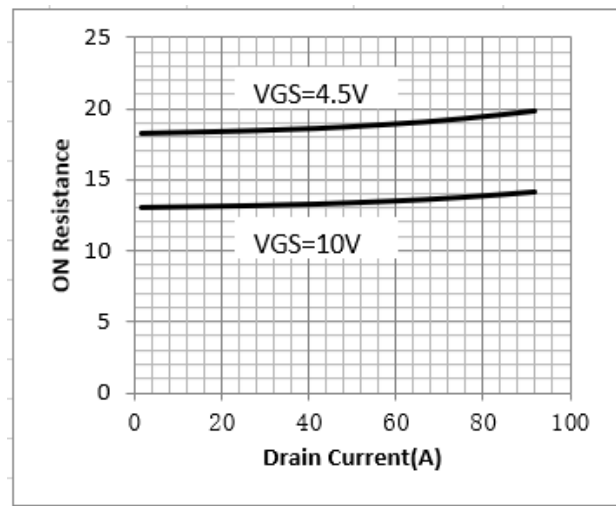


Fig.5 On-Resistance VS Gate Source Voltage

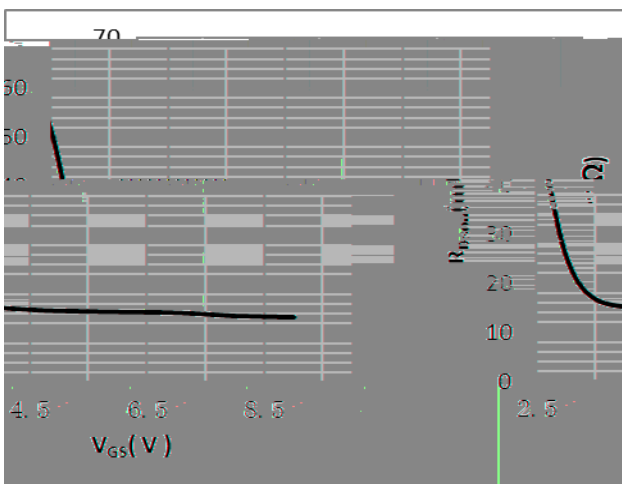
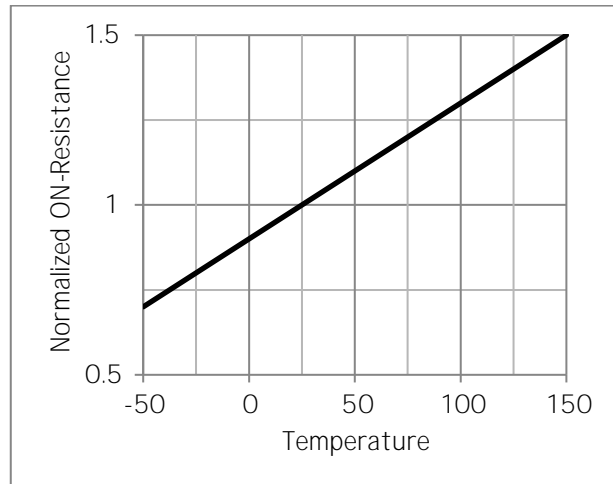


Fig.6 On-Resistance V.S Junction Temperature



P Channel characteristics curve

Fig.1 Power Dissipation Derating Curve

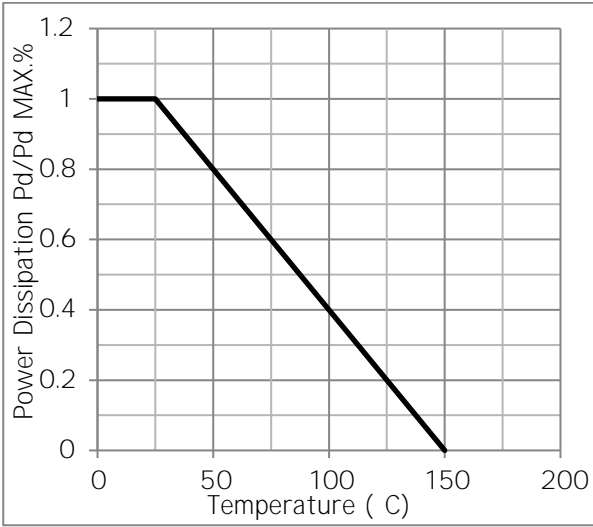


Fig.2 Typical output Characteristics

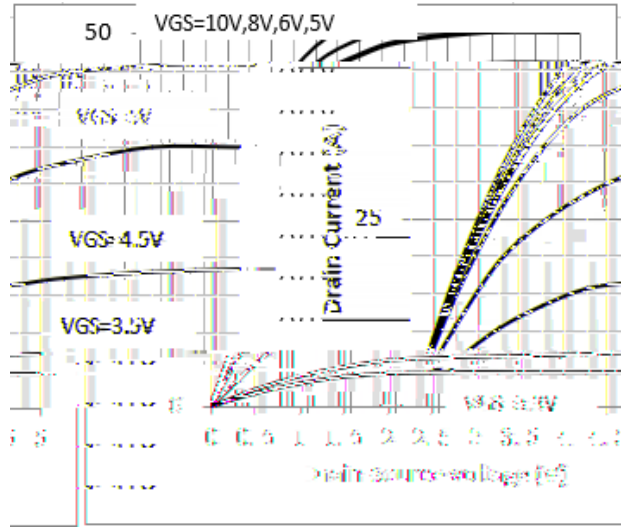


Fig.3 Threshold Voltage V.S Junction Temperature

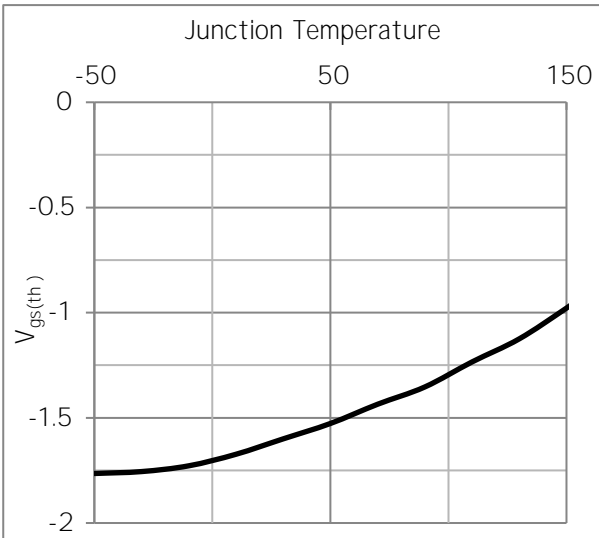


Fig.4 Resistance V.S Drain Current

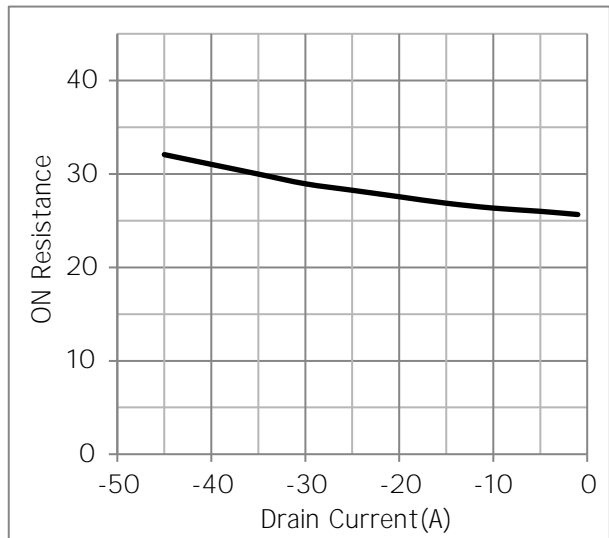


Fig.5 On-Resistance VS Gate Source Voltage

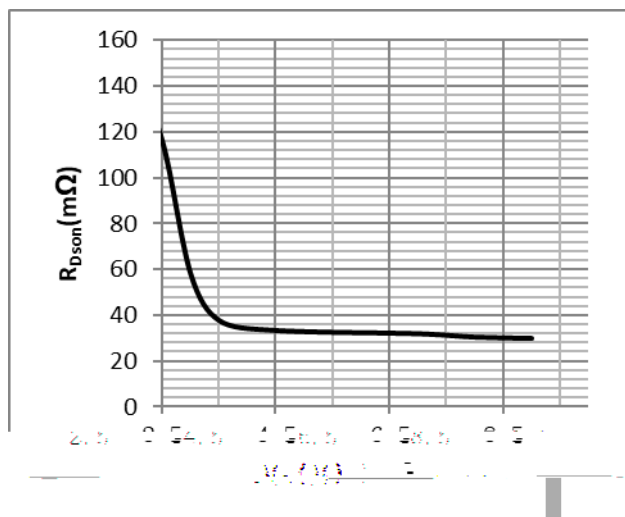
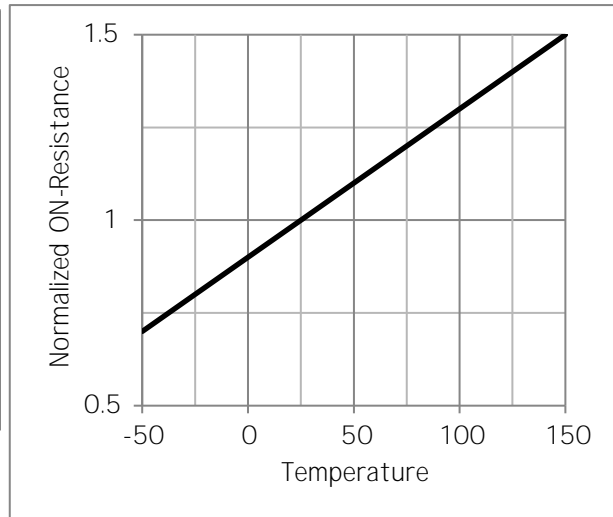


Fig.6 On-Resistance V.S Junction Temperature



Test Circuit

Fig.1 Switching Time Measurement Circuit

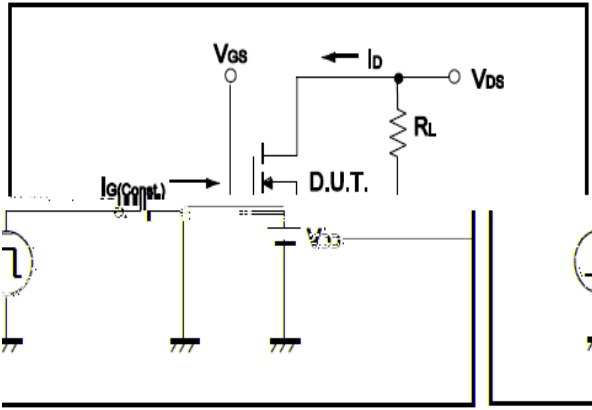


Fig.2 Gate Charge Waveform

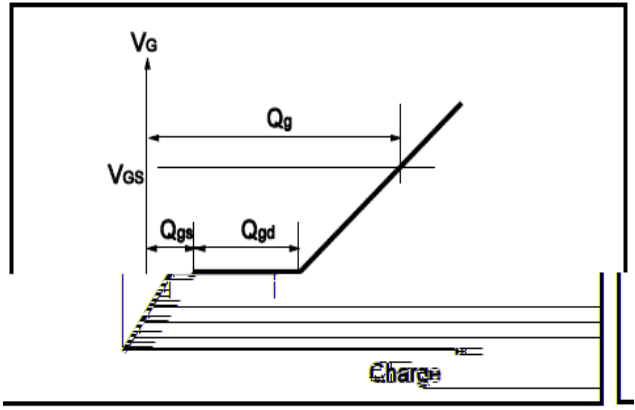


Fig.3 Switching Time Measurement Circuit

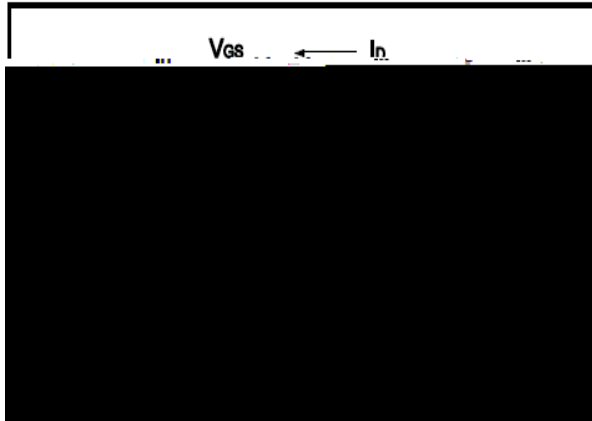


Fig.4 Gate Charge Waveform

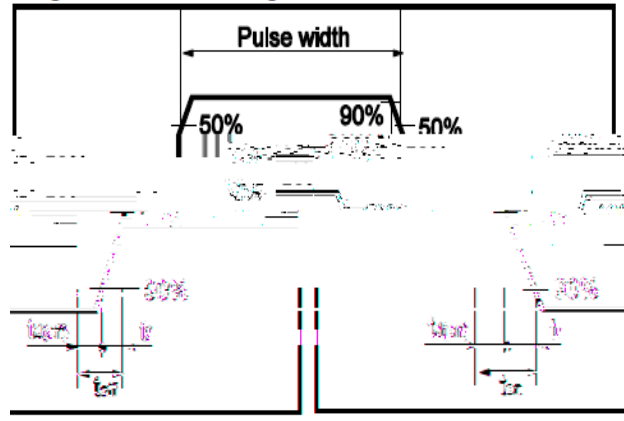


Fig.5 Avalanche Measurement Circuit

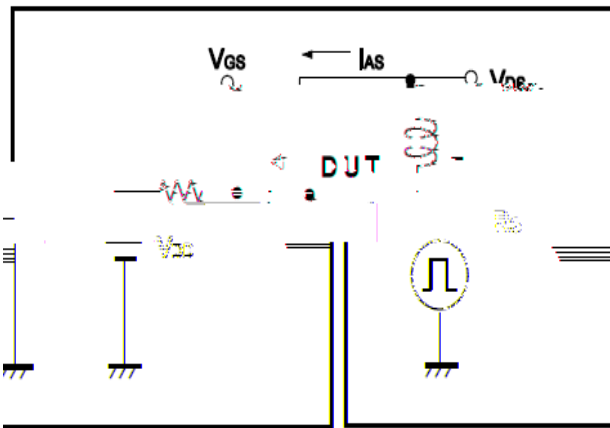


Fig.6 Avalanche Waveform

